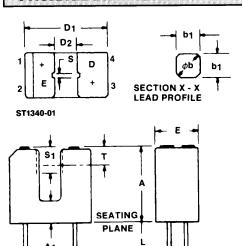


H22A1/2/3

PACKAGE DIMENSIONS

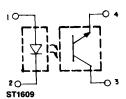


SYMBOL	MILLIMETERS		INC	NOTES		
UTWIDOL	MIN.	MAX.	MIN.	MAX.	INO ILO	
Α	10.7	11.0	.422	.433		
A,	3.0	3.2	.119	.125		
₩b	.600	.750	.024	.030	2	
b,	.50 NOM.		.020 NOM.		2	
D,	11.6	12.0	.457	.472		
D ₂	3.0	3.3	.119	.129		
e,	6.9	7.5	.272	.295		
e ₂	2.3	2.8	.091	.110		
E	6.15	6.35	.243	.249		
L	8.00		.315			
S	.85	1.0	.034	.039		
S ₁	3.45	3.75	.136	.147		
Т	2.6 NOM.		.103	3		

NOTES:

- 1. INCH DIMENSIONS ARE DERIVED FROM MILLIMETERS. 2. FOUR LEADS. LEAD CROSS SECTION IS CONTROLLED BETWEEN 1.27mm (.050") FROM SEATING PLANE AND THE END OF THE LEADS.
- 3. THE SENSING AREA IS DEFINED BY THE "S" DIMENSION AND BY DIMENSION "T" ±0.75mm (±.030 INCH).

PACKAGE OUTLINE



ST1340-02

DESCRIPTION

The H22A Slotted Optical Switch is a gallium arsenide light emitting diode coupled to a silicon photodarlington in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High I_{C(ON)}



Storage Temperature	55°C to +100°C
Operating Temperature	55°C to +100°C
Soldering: Lead Temperature (Iron) Lead Temperature (Flow)	
INPUT DIODE	
Continuous Forward Current	60 mA
Reverse Voltage	
Power Dissipation	100 mW ^c
OUTPUT TRANSISTOR	
Collector-Emitter Voltage	30 Volts
Emitter-Collector Voltage	
Power Dissipation	150 mW

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
Forward Voltage	$V_{\scriptscriptstyle F}$			1.7	V	$I_{\scriptscriptstyle F}=60~\text{mA}$
Reverse Breakdown Voltage	V _R	6.0			٧	$I_R = 10\mu A$
Reverse Leakage Current	I _R	_		1.0	μΑ	V _R = 3 V
OUTPUT TRANSISTOR						
Emitter-Collector Breakdown	BV_{ECO}	6.0		_	V	$I_E = 100 \ \mu A, Ee = 0$
Collector-Emitter Breakdown	BV _{CEO}	30	-	_	V	I _c = 1 mA, Ee = 0
Collector-Emitter Leakage	I _{CEO}	_		100	nA	V _{CE} = 25 V, Ee = 0
COUPLED						
On-State Collector Current	I _{C(ON)}		See page 3.		mA	
Saturation Voltage	V _{CE(SAT)}		See page 3.		V	
Turn-On Time	t _{on}		See page 3.		μS	
Turn-Off Time	t _{off}		See page 3.	, ×	μS	

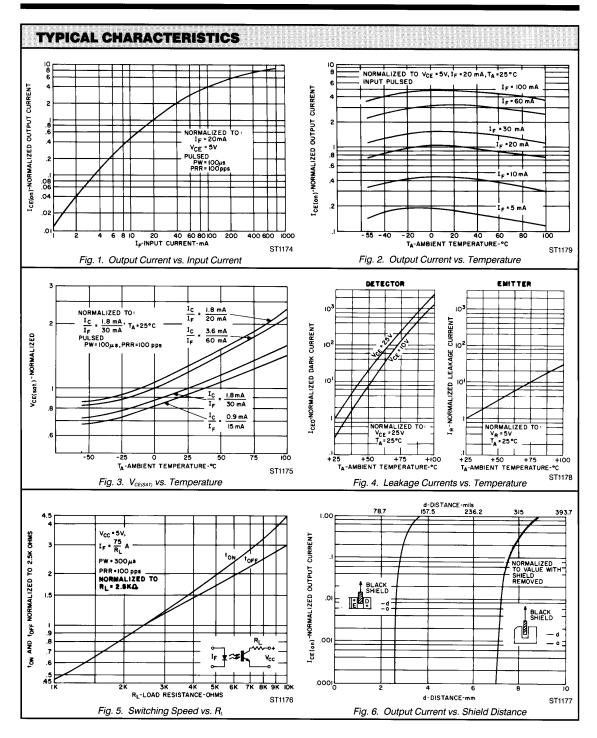
NOTES

- Derate power dissipation linearly 1.33 mW/°C above 25°C.
 Derate power dissipation linearly 2.00 mW/°C above 25°C.
 RMA flux is recommended.
- Methanol or Isopropyl alcohols are recommended as cleaning agents.
 Soldering iron tip 1/16" (1.6 mm) from housing.



I _{cioni} , V _{ce(sat)} , t _{on} , AND t _{off}						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
ON-STATE COLLECTOR	CURRENT					
H22A1	I _{G(ON)}	0.15	_	_	mA	$I_F = 5mA$, $V_{CE} = 5V$
H22A2	I _{C(ON)}	0.30	_	_	mA	$I_F = 5$ mA, $V_{CE} = 5$ V
H22A3	I _{C(ON)}	0.60	_		mA	$I_F = 5$ mA, $V_{CE} = 5$ V
H22A1	I _{C(ON)}	1.0	_	_	mA	$I_F = 20$ mA, $V_{CE} = 5$ V
H22A2	I _{C(ON)}	2.0	_	_	mA	$I_F = 20$ mA, $V_{CE} = 5$ V
H22A3	I _{C(ON)}	4.0			mA	$I_{\scriptscriptstyle F}=20mA,V_{\scriptscriptstyle CE}=5V$
H22A1	I _{C(ON)}	1.9		_	mA	$I_F = 30$ mA, $V_{CE} = 5$ V
H22A2	I _{C(ON)}	3.0	_		mA	$I_F = 30 \text{mA}, V_{CE} = 5 \text{V}$
H22A3	I _{C(ON)}	5.5			mA	$I_F = 30 \text{mA}, V_{CE} = 5 \text{V}$
SATURATION VOLTAGE						
H22A2	$V_{CE(SAT)}$	_	_	0.40	٧	$I_F = 20mA, I_C = 1.8mA$
H22A3	$V_{\text{CE(SAT)}}$		_	0.40	V	$I_F = 20 \text{mA}, I_C = 1.8 \text{mA}$
H22A1	V _{CE(SAT)}			0.40	. V	$I_F = 30\text{mA}, I_C = 1.8\text{mA}$
Turn-On Time	t _{on}		8		μS	$V_{cc} = 5V$, $I_F = 30$ mA, $R_L = 2.5$ Ks
Turn-Off Time	t _{off}		50	_	μS	$V_{cc} = 5V$, $I_F = 30$ mA, $R_I = 2.5$ Ks







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